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UNITED STATE DEPARTMENT OF COMMERCE Patent and Trademark Office

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FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.

09/730,875 12/05/00 ISHIDA S 2933SE-64-CO

DOUGLAS W. SWARTZ SHERIDAN ROSS P.C. 1560 BROADWAY, SUITE 1200 DENVER CO 80202-5141

APPLICATION NO.

ART UNIT PAPER NUMBER
2811

EXAMINER

DATE MAILED:

LOKE, S

10/25/01

Please find below and/or attached an Office communication concerning this application or proceeding.

MM41/1025

Commissioner of Patents and Trademarks

•							
		Application No. Applicant(s)					
Office Action Summary		09/730,87	5	ISHIDA ET AL.			
		Examiner		Art Unit			
		Steven Lo		2811			
Period fo	The MAILING DATE of this communication app r Reply	ears on the	cover sheet with the c	orrespondence address			
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). - Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). Status							
1)🖂	Responsive to communication(s) filed on 05 L	December 2	<u> 2000</u> .				
2a) <u></u> □	This action is FINAL . 2b)⊠ Thi	is action is	non-final.				
3)	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Dispositi	on of Claims						
4) 🖾	4) Claim(s) 1 is/are pending in the application.						
	4a) Of the above claim(s) is/are withdrav	vn from co	nsideration.				
5)	5) Claim(s) is/are allowed.						
6)⊠	6)⊠ Claim(s) <u>1</u> is/are rejected.						
7)	7) Claim(s) is/are objected to.						
8)□	Claim(s) are subject to restriction and/or	r election re	equirement.				
Applicati	on Papers						
•	9)☐ The specification is objected to by the Examiner.						
10) 🗌 -	10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.						
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11)[11) The proposed drawing correction filed on is: a) approved b) disapproved by the Examiner.						
40)[7] -	If approved, corrected drawings are required in reply to this Office action.						
7—	The oath or declaration is objected to by the Exa	ammer.					
-	inder 35 U.S.C. §§ 119 and 120		d05110.0 \$ 440/o) (d) or (f)			
•	13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a)[All b) Some * c) None of: ∴	- h h	id	•			
	1. Certified copies of the priority documents			on No. 00/024 955			
•	2. Certified copies of the priority documents						
	 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
14)∐ A	Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).						
,	a) The translation of the foreign language provisional application has been received. 5) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.						
Attachment(s)							
2) Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s) <u>2</u>		4) Interview Summary 5) Notice of Informal F 6) Other:	(PTO-413) Paper No(s) Patent Application (PTO-152)			

U.S. Patent and Trademark Office PTO-326 (Rev. 04-01)

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The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

Claim 1 is rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

The written description never discloses the polycrystalline silicon film being formed by irradiating a laser beam on a surface of an amorphous silicon film to heat the amorphous film as claimed in claim 1.

The written description never discloses the laser beam is scanned on the surface of the amorphous silicon film such that laser energy increases in order of the substrate, one of the pair of tapered end portions, and the center portion as claimed in claim 1.

Claim 1 is rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to enable one skilled in the art to which it pertains, or with which it is most nearly connected, to make and/or use the invention.

The specification also never discloses how a uniform grain size of the polycrystalline silicon film is acquired by securing a gate withstand voltage of the thin film transistor and preventing the inclined surfaces of the pair of tapered end portions from increasing as claimed in claim 1.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

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(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 1 insofar, as in compliance with 35 USC 112, is rejected under 35 U.S.C. 103(a) as being unpatentable over Tsai et al. in view of Ono et al. (PTO-1449).

Tsai et al. discloses a thin film transistor in fig. 11. It comprises: an insulator substrate [71]; a gate electrode [72] located on the insulator substrate; a gate insulator film [73] provided above the insulator substrate and the gate electrode; and a polycrystalline silicon film [74, 176] located on the gate insulator film, the polycrystalline silicon film being formed by laser annealing step on a surface of an amorphous layer; the gate electrode having a center portion with a flat surface.

Tsai et al. differs from the claimed invention by not showing a pair of tapered end portions with inclined surfaces and an angle between each of the inclined surfaces of the pair of tapered end portions and a surface of the insulator substrate being set within a range of 5 to 40 degrees.

Ono et al. shows a tapered end portion with inclined surface and an angle between the inclined surface of the tapered end portion and a surface of the insulator substrate being set to a range of 6 to 10 degrees (col. 18, lines 1-11).

Since both Tsai et al. and Ono et al. teach a thin film transistor with a bottom gate electrode, it would have been obvious to have the tapered end portion of the gate electrode of Ono et al. in each side of the gate electrode of Tsai et al. because it prevents the crack of the overlaying portion of the insulating film.

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It is inherent that the combined device would show a uniform grain size of the polycrystalline silicon film is acquired by securing a gate withstand voltage of the thin film transistor and preventing the inclined surfaces of the pair of tapered end portions from increasing. It is also inherent that the laser beam is scanned on the surface of the amorphous silicon film such that laser energy increases in order of the substrate, one of the pair of tapered end portions, and the center portion.

The process limitation of how the polycrystalline silicon film is formed have no patentable weight in claim drawn to structure. It is important to note that there are many ways to form a polycrystalline silicon film. Therefore, the phrases "formed by irradiating a laser beam on a surface of an amorphous silicon film to heat the amorphous film" and "the laser beam is scanned on the surface of the amorphous silicon film such that laser energy increases in order of the substrate, one of the pair of tapered end portions, and the center portion" are thus non-limiting.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven Loke whose telephone number is (703) 308-4920. The examiner can normally be reached on 7:45 am to 5:15 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (703) 308-2772. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7722 for After Final communications.

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Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

sl September 30, 2001 Steven Loke Primary Examiner

Steven Sohe